Nov. 2005

THE SPECIFICATION OF INFRARED LED CHIP "FP6R"

1. DESCRIPTION

This is a GaAs LED chip. It is P-side up. The peak wavelength is 940 nm (Typ.).

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25deg. C)

CONDITION			MIN.	TYP.	MAX.	UNIT
Forward Voltage	(Vf)	IF=20mA		1.17		V
Reverse Voltage	(Vr)	IR=10uA	5			V
Radiated Power[1)]	(Po)	IF=20mA	0.5			mW
Peak Wavelength	(λp)	IF=20mA		940		nm
Spectral Radiation Bandwidth	(Δλ)	IF=20mA		45		nm

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

Continuous Maximum Forward Current : 50 mA(DC)
Reverse Voltage : 5 V(IR=10uA)
Storage Temperature
while on mylar membrane : 0 to 40 deg. C
after removal from mylar membrane : -40 to 100 deg. C

4. PHYSICAL CHRACTERISTICS AND STRUCTURE

1) Material : GaAs
2) Structure : HOMO Structure
3) Junction Size : 0.370mm×0.370mm
4) Thickness : 0.280mm
5) Bond Pad Size : 0.115mm diameter
6) Anode Metallization : Gold Alloy
7) Cathode Metallization: Gold Alloy

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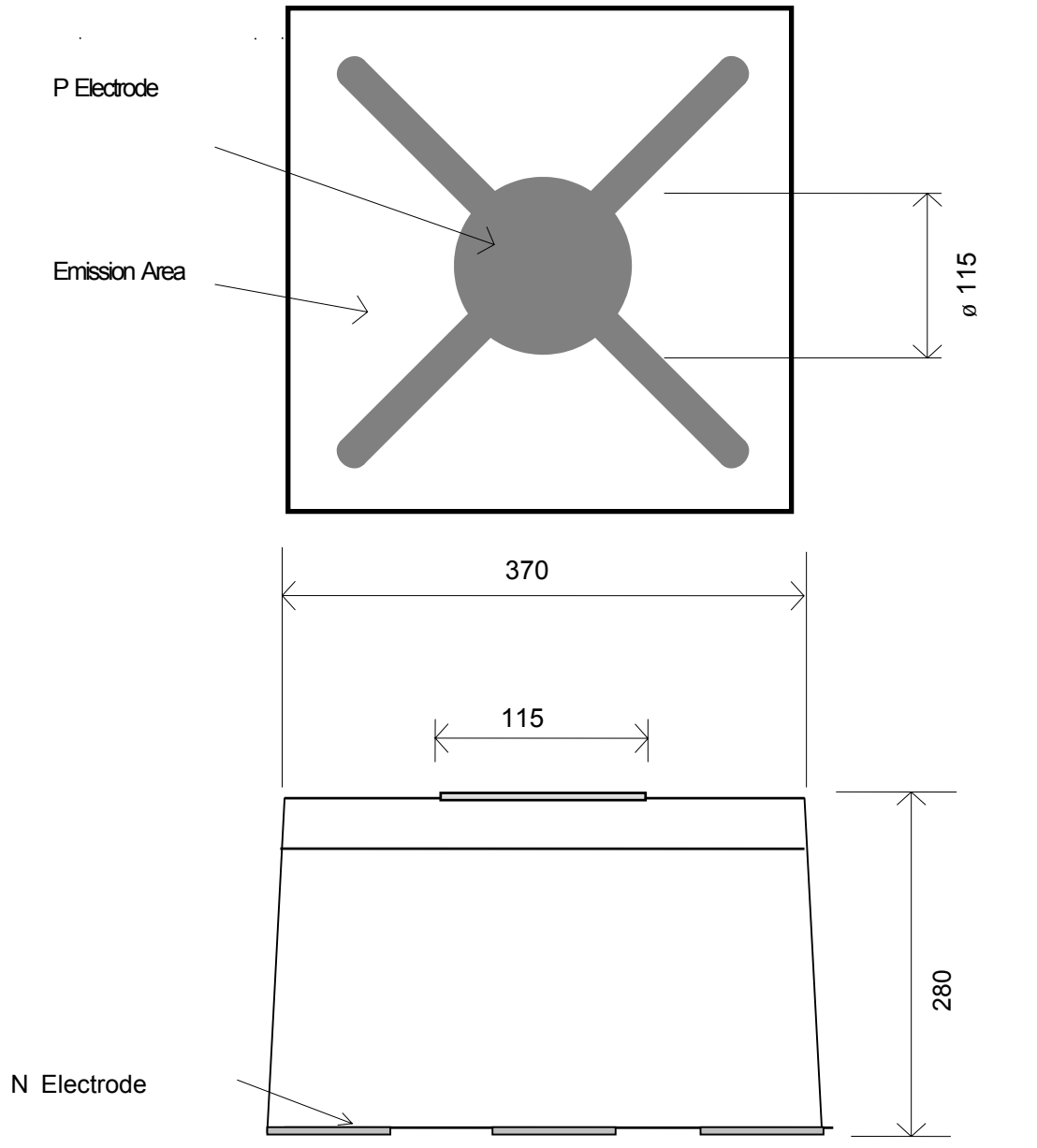
Physical Dimensions

Model FP6R

UNIT:um



Remark: This specification is for reference purpose only, and subject to change without prior notice.
Approved specification shall be obtained for the regular purchase.